



#### 100V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	Max R <sub>DS(on)</sub> Max R <sub>DS(on)</sub> Max R <sub>DS(on)</sub> Max I <sub>D</sub> T <sub>A</sub> = +25°  (Note 7)		
100V	230mΩ @ V <sub>GS</sub> = 10V	1.9A	
	$300 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	1.68A	

### **Description and Applications**

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. It is ideal for high-efficiency, low voltage, power management applications.

- DC DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

### **Features and Benefits**

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- SOT26 Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability
- PPAP Available (Note 4)

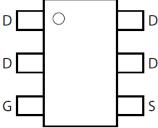
#### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.015 grams (Approximate)

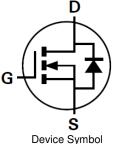




Top View







### Ordering Information (Note 5)

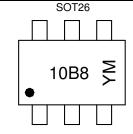
Part Number	Compliance	Case	Packing
ZXMN10B08E6QTA	Automotive	SOT26	3,000
ZXMN10B08E6QTC	Automotive	SOT26	10,000

Pinout Top-View

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



10B8 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2015	201	16	2017	2018	2019	2020	2021	20	22 2	2023	2024	2025
Code	С	D	)	Е	F	G	Н	I	,	J	K	L	М
Month	n J	an	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code		1	2	2	1	5	6	7	0	۵		NI	D



### Maximum Ratings (@TA = +25 ℃, unless otherwise specified.)

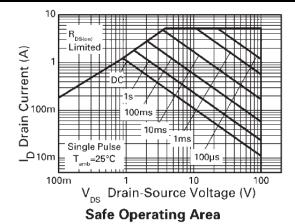
Chara	cteristic		Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	100	V
Gate-Source Voltage			$V_{GS}$	±20	V
		(Note 7)	ID	1.9	
Continuous Drain Current	$V_{GS} = 10V$	T <sub>A</sub> = +70 °C (Note 7)		1.5	Α
		(Note 6)		1.6	
Pulsed Drain Current		(Note 8)	I <sub>DM</sub>	9	Α
Continuous Source Current (Body	Diode)	(Note 7)	Is	2.5	Α
Pulsed Source Current (Body Diod	e)	(Note 8)	I <sub>SM</sub>	9	Α

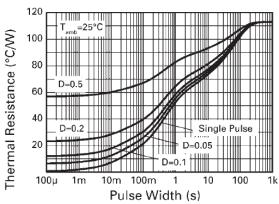
### Thermal Characteristics (@TA = +25 °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation (Note 6)		$P_{D}$	1.1	W	
Linear Derating Factor			8.8	mW/℃	
Power Dissipation (Note 7)	D-	1.7	W		
Linear Derating Factor	$P_{D}$	13.6	mW/°C		
Thermal Resistance, Junction to Ambient	(Note 6)	В	113	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	73	C/VV	
Operating and Storage Temperature Range	$T_{J}, T_{STG}$	-55 to +150	℃		

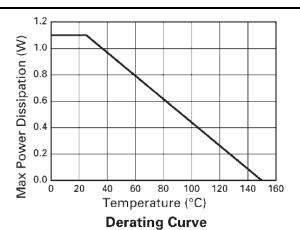
Notes:

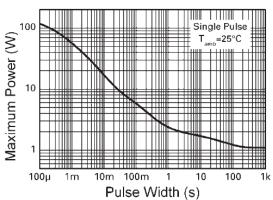
### **Thermal Characteristics**





**Transient Thermal Impedance** 





**Pulse Power Dissipation** 

<sup>6.</sup> For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
7. For a device surface mounted on FR4 PCB measured at t ≤ 5 secs.
8. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300µs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.



## Electrical Characteristics (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

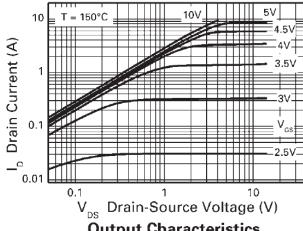
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	0.5	μΑ	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	_	3.0	V	$I_D=250\mu A,V_{DS}=V_{GS}$
				0.23		$V_{GS} = 10V, I_D = 1.6A$
Static Drain-Source On-Resistance (Note 9)	R <sub>DS(ON)</sub>		_	0.30	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 1.4A
				0.50		$V_{GS} = 4.3V, I_D = 1.1A$
Forward Transconductance (Notes 9 & 11)	<b>g</b> fs	_	4.8	_	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 1.6A
Diode Forward Voltage (Note 9)	$V_{SD}$	_	0.85	0.95	V	$T_J = +25$ °C, $I_S = 2.0$ A, $V_{GS} = 0$ V
DYNAMIC CHARACTERISTICS (Note 11)						
Input Capacitance	C <sub>iss</sub>	_	497		рF	
Output Capacitance	Coss	_	29	_	pF	$V_{DS} = 50V, V_{GS} = 0V$ of = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	18		pF	1 = 1.0Wii 12
Gate Charge (Note 10)	Qg	_	5.0		nC	$V_{DS} = 50V$ , $V_{GS} = 5V$ , $I_{D} = 1.6A$
Total Gate Charge (Note 10)	Qg	_	9.2	_	nC	
Gate-Source Charge (Note 10)	Q <sub>gs</sub>	_	1.7	_	nC	$V_{DS} = 50V, V_{GS} = 10V,$
Gate-Drain Charge (Note 10)	Q <sub>gd</sub>	_	2.5	_	nC	-I <sub>D</sub> = 1.6A
Turn-On Delay Time (Note 10)	t <sub>d(on)</sub>	_	2.9	_	ns	
Turn-On Rise Time (Note 10)	t <sub>r</sub>	_	2.1	_	ns	$V_{DD} = 50V, I_D = 1.0A,$
Turn-Off Delay Time (Note 10)	t <sub>d(off)</sub>	_	12.1	_	ns	$R_G \cong 6.0\Omega$ , $V_{GS} = 10V$
Turn-Off Fall Time (Note 10)	t <sub>f</sub>	_	5.0	_	ns	]
Reverse Recovery Time	t <sub>rr</sub>		32	_	ns	T <sub>J</sub> = +25 °C, I <sub>F</sub> = 1.7A,
Reverse Recovery Charge	Q <sub>rr</sub>	_	40	_	nC	di/dt = 100A/μs

Notes:

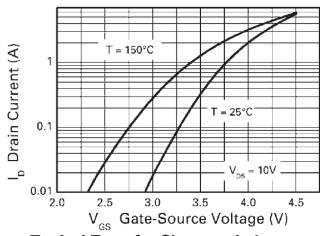
- 9. Measured under pulsed conditions. Width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%. 10. Switching characteristics are independent of operating junction temperature. 11. For design aid only, not subject to production testing.



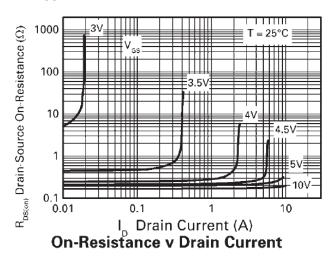
## **Typical Characteristics**

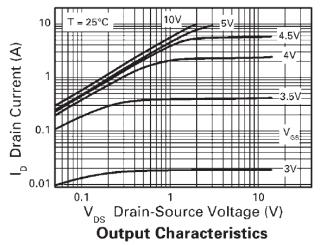


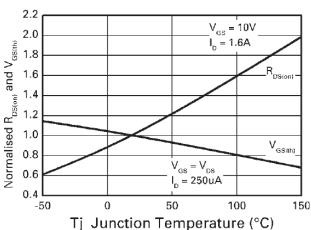




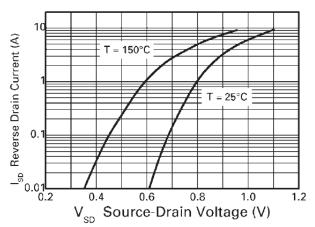
**Typical Transfer Characteristics** 







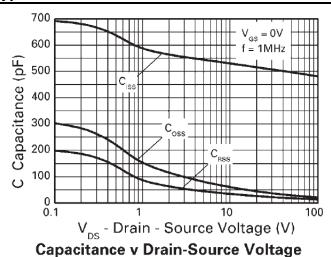
Normalised Curves v Temperature

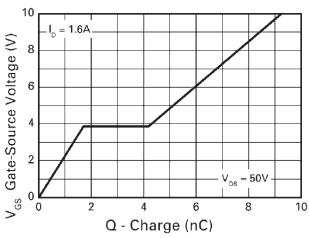


Source-Drain Diode Forward Voltage



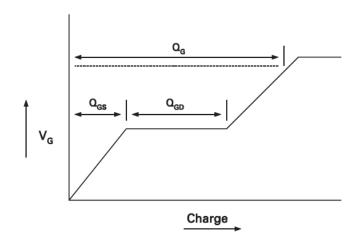
### Typical Characteristics (continued)

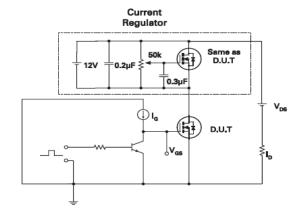




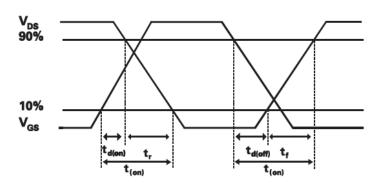
Gate-Source Voltage v Gate Charge

## **Test Circuits**

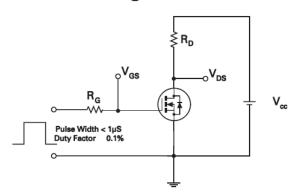




## **Basic Gate Charge Waveform**



**Gate Charge Test Circuit** 



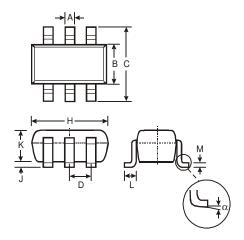
**Switching Time Waveforms** 

**Switching Time Test Circuit** 



# **Package Outline Dimensions**

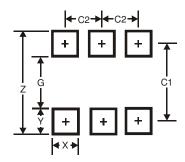
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26							
Dim	Min	Max	Тур					
Α	0.35	0.50	0.38					
В	1.50	1.70	1.60					
С	2.70	3.00	2.80					
D	_		0.95					
Н	2.90	3.10	3.00					
J	0.013	0.10	0.05					
K	1.00	1.30	1.10					
L	0.35	0.55	0.40					
М	0.10	0.20	0.15					
α	0°	8°	_					
All D	imensi	ons in	mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Υ	0.80
C1	2.40
C2	0.95



#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### **LIFE SUPPORT**

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2015, Diodes Incorporated

www.diodes.com